

NCE N-Channel Super Trench II Power MOSFET

Description

The series of devices uses **Super Trench II** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{\text{DS(ON)}}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

Application

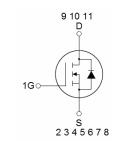
- DC/DC Converter
- •Ideal for high-frequency switching and synchronous rectification

General Features

- V_{DS} =100V, I_D =330A $R_{DS(ON)}$ =1.5m Ω , typical @ V_{GS} =10V
- Excellent gate charge x R_{DS(on)} product(FOM)
- Very low on-resistance R_{DS(on)}
- 175 °C operating temperature
- Pb-free lead plating

100% UIS TESTED! 100% ΔVds TESTED!





Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP020N10LL	NCEP020N10LL	TOLL	-	-	-

Absolute Maximum Ratings (T_C=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	VDS	100	V
Gate-Source Voltage	V _G s	±20	V
Drain Current-Continuous (T _C =25 °C)	I _D (T _C =25℃)	330	А
Drain Current-Continuous(T _C =100℃)	I _D (T _C =100℃)	240	Α
Drain Current-Continuous (T _A =25°C)	I _D (T _A =25℃)	29.5	Α
Pulsed Drain Current (Note 1)	I _{DM}	1320	Α
Maximum Power Dissipation (T _C =25 ℃)	P _D (T _C =25°C)	400	W
Maximum Power Dissipation (T _A =25 °C)	P _D (T _A =25°C)	3.75	W
Derating factor		2.67	W/℃
Single pulse avalanche energy (Note 4)	E _{AS}	2784	mJ
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 175	$^{\circ}$

Thermal Characteristic

Thermal Resistance, Junction-to-Case	Rejc	0.38	°C/W	
Thermal Resistance,Junction-to-Ambient (Note 2)	$R_{\theta JA}$	40	°C/W	



Electrical Characteristics (T_C=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	n-Source Breakdown Voltage BV _{DSS} V _{GS} =0V I _D =250μA		100		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V,V _{GS} =0V	-	-	1	μΑ
Gate-Body Leakage Current	I _{GSS}	V_{GS} =±20 V , V_{DS} =0 V	-	-	±100	nA
On Characteristics (Note 2)						
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	2.0	3.0	4.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =165A	-	1.5	2.0	mΩ
Gate resistance	R _G	F=1.0MHz	-	2.8	-	Ω
Forward Transconductance	g FS	V _{DS} =5V,I _D =165A		200	-	S
Dynamic Characteristics (Note3)						
Input Capacitance	C _{lss}	\/ F0\/\/ 0\/	-	17000	-	PF
Output Capacitance	C _{oss}	V_{DS} =50V, V_{GS} =0V,	-	1500	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0MHz	-	77	-	PF
Switching Characteristics (Note 3)						
Turn-on Delay Time	t _{d(on)}		-	37	-	nS
Turn-on Rise Time	t _r	V_{DD} =50 V , I_{D} =165 A	-	29	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10 V , R_{G} =1.6 Ω	-	82	-	nS
Turn-Off Fall Time	t _f		-	34	-	nS
Total Gate Charge	Qg	\/ _E0\/ _40EA	-	252	-	nC
Gate-Source Charge	Q _{gs}	V _{DS} =50V,I _D =165A,	-	72		nC
Gate-Drain Charge	Q _{gd}	V _{GS} =10V	-	63		nC
Drain-Source Diode Characteristics			•			
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =165A	-		1.2	V
Diode Forward Current (Note 2)	Is		-	-	330	Α
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = 165A	-	105	-	nS
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note2)}$	-	290	-	nC

Notes:

^{1.} Repetitive Rating: Pulse width limited by maximum junction temperature.

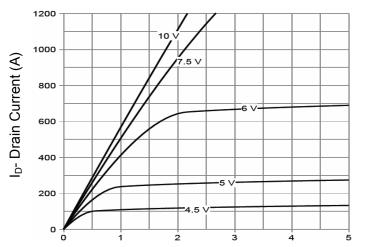
^{2.} The value of R_{BJA} is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25° C. The value in any given application depends on the user's specific board design, and the maximum temperature of 175° C may be used if the PCB allows it.

^{3.} Guaranteed by design, not subject to production

^{4.} EAS condition : Tj=25 $^{\circ}\text{C}$,VDD=50V,VG=10V,L=0.5mH,Rg=25 Ω

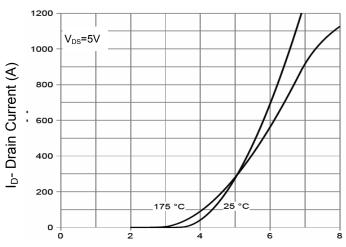


Typical Electrical and Thermal Characteristics



Vds Drain-Source Voltage (V)





Vgs Gate-Source Voltage (V)

Figure 2 Transfer Characteristics

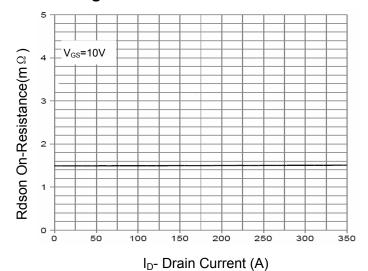
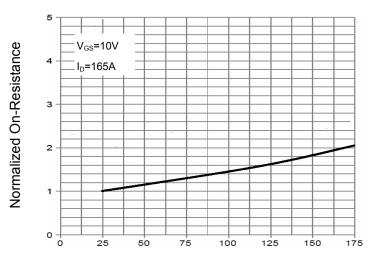


Figure 3 Rdson- Drain Current



T_J-Junction Temperature(°C)

Figure 4 Rdson-Junction Temperature

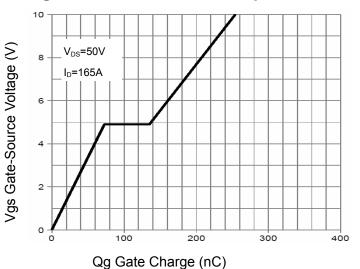
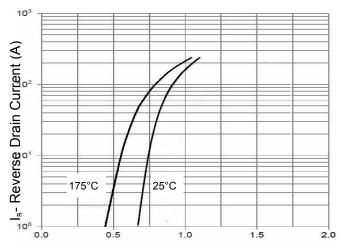


Figure 5 Gate Charge



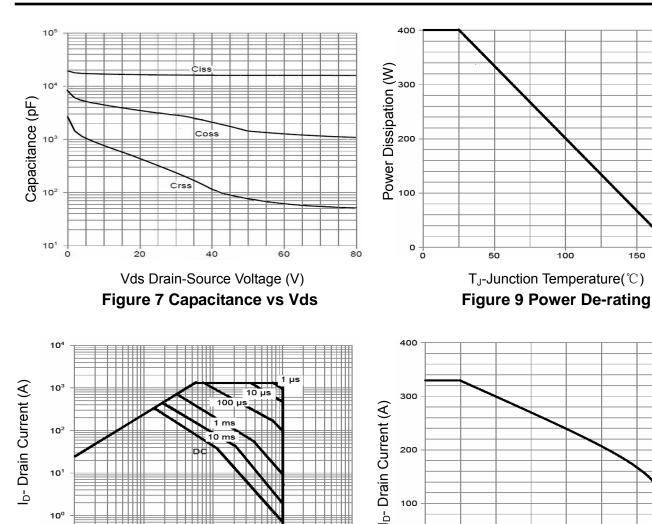
Vsd Source-Drain Voltage (V)

Figure 6 Source- Drain Diode Forward

200

200





Vds Drain-Source Voltage (V)
Figure 8 Safe Operation Area

 T_J -Junction Temperature (°C) Figure 10 Current De-rating

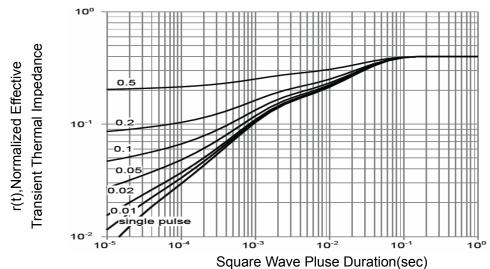


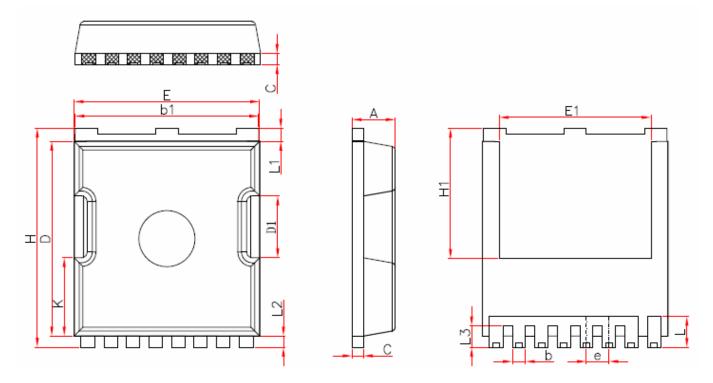
Figure 11 Normalized Maximum Transient Thermal Impedance

10⁻¹



TOLL Package Information

Wuxi NCE Power Co., Ltd



Symbo1	Мi	ers			
	Min.	Nom.	Max.		
A	2.20	2.30	2.40		
b	0.65	0.75	0.85		
b1	9.70	9.80	9.90		
С	0.50	0.60	0.70		
D	10.30	10.40	10.50		
D1	3.15	3.3	3. 45		
Е	9.70	9.90	10.10		
E1	8.00	8.10	8. 20		
е	1.10	1.20	1.30		
Н	11.6	11.7	11.8		
H1	6.85	6.95	7.05		
K	4.08	4.18	4. 28		
L	1.60	1.65	2.10		
L1	0.60	0.70	0.80		
L2	0.50	0.60	0.70		
L3	1.05	1.20	1.30		



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